

Features

- ◆ 16K x 15 Configuration
 - 12 TAG Bits
 - 3 Separate I/O Status Bits (Valid, Dirty, Write Through)
- ◆ Match output uses Valid bit to qualify MATCH output
- ◆ High-Speed Address-to-Match comparison times
 - 8/9/10/12ns over commercial temperature range
- ◆ **BRDY** circuitry included inside the Cache-Tag for highest speed operation
- ◆ Asynchronous Read/Match operation with Synchronous Write and Reset operation
- ◆ Separate **WE** for the TAG bits and the Status bits
- ◆ Separate **OE** for the TAG bits, the Status bits, and **BRDY**
- ◆ Synchronous **RESET** pin for invalidation of all Tag entries
- ◆ Dual Chip selects for easy depth expansion with no performance degradation
- ◆ I/O pins both 5V TTL and 3.3V LVTTTL compatible with Vcc pins
- ◆ **PWRDN** pin to place device in low-power mode
- ◆ Packaged in a 80-pin Thin Plastic Quad Flat Pack (TQFP).

Description

The IDT71215 is a 245,760-bit Cache Tag Static RAM, organized 16K x 15 and designed to support the Pentium and other Intel processors at bus speeds up to 66MHz. There are twelve common I/O TAG bits, with the remaining three bits used as status bits. A 12-bit comparator is on-chip to allow fast comparison of the twelve

stored TAG bits and the current Tag input data. An active HIGH MATCH output is generated when these two groups of data are the same for a given address. This high-speed MATCH signal, with tADM as fast as 8ns, provides the fastest possible enabling of secondary cache accesses.

The three separate I/O status bits (VLD, DTY, and WT) can be configured for either dedicated or generic functionality, depending on the SFUNC input pin. With SFUNC LOW, the status bits are defined and used internally by the device, allowing easier determination of the validity and use of the given Tag data. SFUNC HIGH releases the defined internal status bit usage and control, allowing the user to configure the status bit information to fit his system needs. A synchronous RESET pin, when held LOW at a rising clock edge, will reset all status bits in the array for easy invalidation of all Tag addresses.

The IDT71215 also provides the option for Burst Ready (BRDY) generation within the cache tag itself, based upon MATCH, VLD bit, WT bit, and external inputs provided by the user. This can significantly simplify cache controller logic and minimize cache decision time. Match and Read operations are both asynchronous in order to provide the fastest access times possible, while Write operations are synchronous for ease of system timing.

The IDT71215 uses a 5V power supply on Vcc with separate Vcco pins provided for the outputs to offer compliance with both 5V TTL and 3.3V LVTTTL Logic levels. The PWRDN pin offers a low-power standby mode to reduce power consumption by 90%, providing significant system power savings.

The IDT71215 is fabricated using IDT's high-performance, high-reliability BiCMOS technology and is offered in a space-saving 80-pin Thin Plastic Quad Flat Pack (TQFP) package.

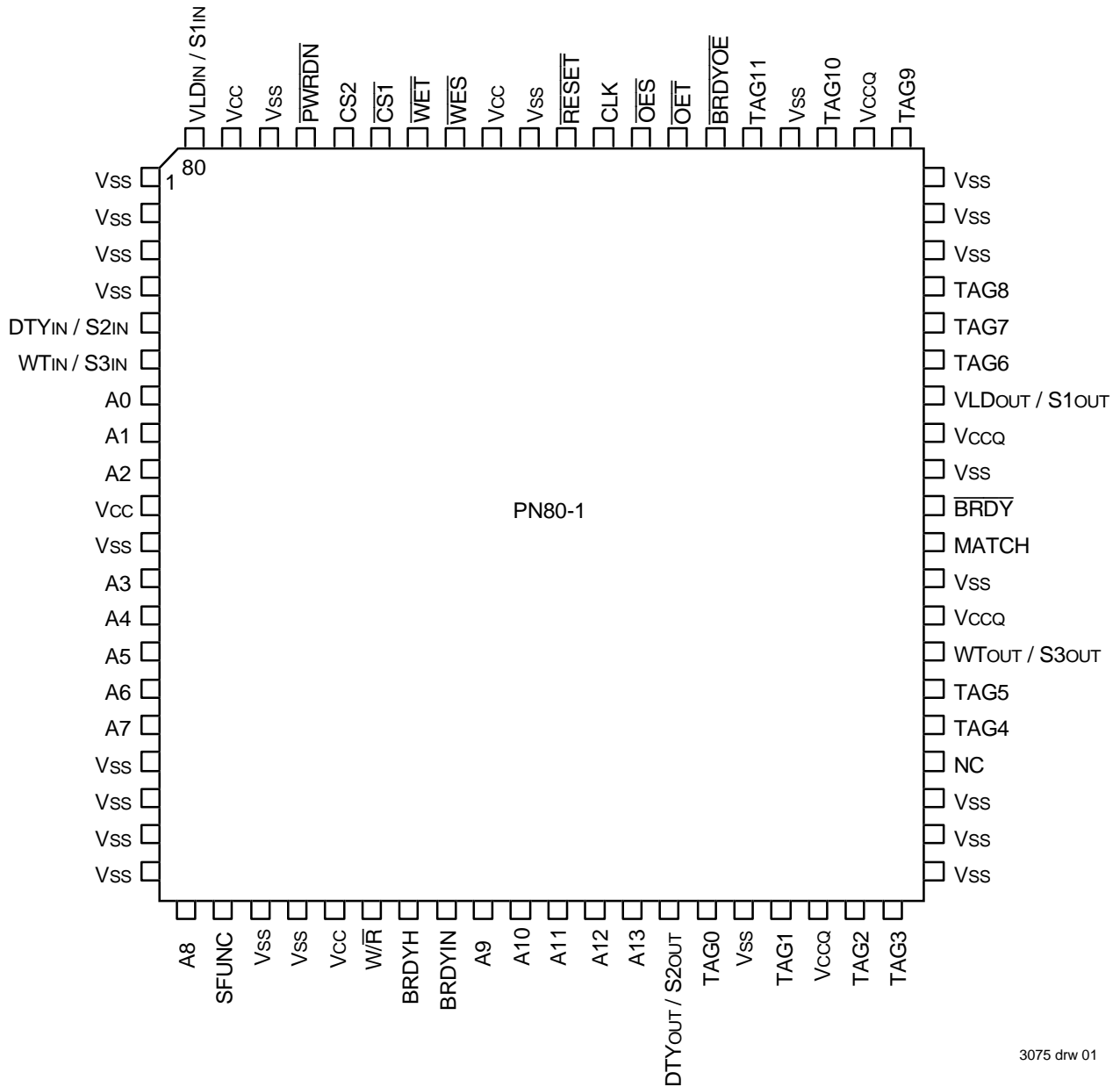
Pin Descriptions

A0 – A13	Address Inputs	Input
CS1, CS2	Chip Selects	Input
WE \overline{T}	Write Enable – Tag Bits	Input
WE \overline{S}	Write Enable – Status Bits	Input
OE \overline{T}	Output Enable – Tag Bits	Input
OE \overline{S}	Output Enable – Status Bits	Input
RESET	Status Bit Reset	Input
PWRDN	Powerdown Mode Control Pin	Input
SFUNC	Status Bit Function Control Pin	Input
W/R	Write/Read Input from Processor	Input
VLDIN/S1IN	Valid Bit/S1 Bit Input	Input
DTYIN/S2IN	Dirty Bit/S2 Bit Input	Input
WTIN/S3IN	Write Through Bit/S3 Bit Input	Input

CLK	System Clock	Input
BRDYH	BRDY Force High	Input
BRDYOE	BRDY Output Enable	Input
BRDYIN	Additional BRDY Input	Input
BRDY	Burst Ready	Output
TAG0 – TAG11	Tag Data Input/Outputs	I/O
VLDOUT/S1OUT	Valid Bit/S1 Bit Output	Output
DTYOUT/S2OUT	Dirty Bit/S2 Bit Output	Output
WTOUT/S3OUT	Write Through Bit/S3 Bit Output	Output
MATCH	Match	Output
Vcc	+5V Power	Pwr
Vcco	Output Buffer Power	QPwr
Vss	Ground	Gnd

3075 tbl 01

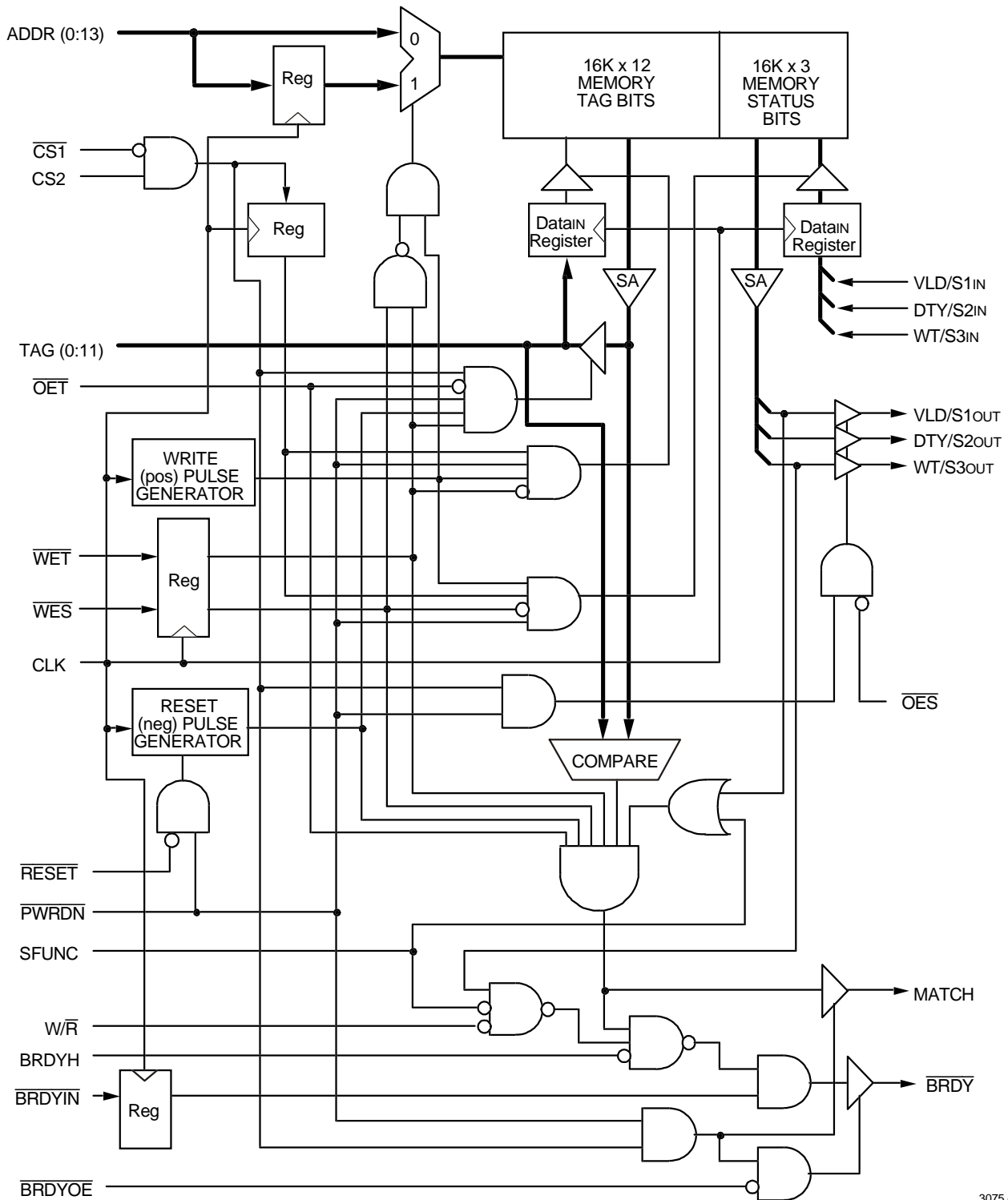
Pin Configuration



**TQFP
 Top View**

3075 drw 01

Functional Block Diagram



3075 drw 02

Truth Table — Chip Select, Reset, and Power-Down Functions^(1,2)

$\overline{CS1}$	CS2	\overline{RESET}	\overline{PWRDN}	CLK	\overline{WET}	\overline{WES}	\overline{BRDYOE}	TAG	VLDOUT	DTYOUT	WTOUT	MATCH	\overline{BRDY}	OPERATION	POWER
CHIP SELECT FUNCTION															
H	X	X	H	X	X	X	X	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Deselected	Active
X	L	X	H	X	X	X	X	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Deselected	Active
L	H	X	H	X	X	X	X	—	—	—	—	—	—	Selected	Active
RESET FUNCTION															
L	H	L	H	↑	H	H	L	Hi-Z	L ⁽³⁾	L ⁽³⁾	L ⁽³⁾	L ⁽³⁾	H	Reset Status	Active
L	H	L	H	↑	H	H	H	Hi-Z	L ⁽³⁾	L ⁽³⁾	L ⁽³⁾	L ⁽³⁾	Hi-Z	Reset Status	Active
H	X	L	H	↑	H	H	X	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Reset Status	Active
X	L	L	H	↑	H	H	X	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Reset Status	Active
X	X	L	H	↑	L	X	X	—	—	—	—	—	—	Not Allowed	—
X	X	L	H	↑	X	L	X	—	—	—	—	—	—	Not Allowed	—
POWER-DOWN FUNCTION															
X	X	X	L	X	H	H	X	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Power-down	Standby

3075 tbl 02

NOTES:

- "H" = V_{IH}, "L" = V_{IL}, "X" = don't care, "-" = unrelated.
- \overline{OET} , \overline{OES} , $\overline{W/R}$, \overline{BRDYH} , \overline{BRDYIN} and SFUNC are "X" for this table.
- \overline{OES} is LOW.

Truth Table — Read and Write Functions^(1,2)

\overline{OET}	\overline{OES}	\overline{WET}	\overline{WES}	CLK	$\overline{W/R}$	TAG	VLDIN	DTYIN	WTIN	VLDOUT	DTYOUT	WTOUT	MATCH	OPERATION
READ FUNCTION														
L	X	H	X	X	X	DOUT	—	—	—	—	—	—	DOUT	Read TAG I/O
X	L	X	X	X	X	—	—	—	—	DOUT	DOUT	DOUT	DOUT	Read Status Bits
H	X	X	X	X	X	Hi-Z	—	—	—	—	—	—	DOUT	TAG I/O Disable
X	H	X	X	X	X	—	—	—	—	Hi-Z	Hi-Z	Hi-Z	DOUT	Status Disabled
WRITE FUNCTION														
H	X	L	X	↑	X	DIN	—	—	—	DOUT	DOUT	DOUT	L	Write TAG I/O
L	X	L	X	↑	X	—	—	—	—	—	—	—	—	Not Allowed
X	L	X	L	↑	X	—	DIN	DIN	DIN	DOUT ⁽³⁾	DOUT ⁽³⁾	DOUT ⁽³⁾	L	Write Status Bits
X	H	X	L	↑	X	—	DIN	DIN	DIN	Hi-Z	Hi-Z	Hi-Z	L	Write Status Bits

3075 tbl 03

NOTES:

- "H" = V_{IH}, "L" = V_{IL}, "X" = don't care, "-" = unrelated.
- This table applies when $\overline{CS1}$ is LOW and CS2, \overline{RESET} , and \overline{PWRDN} are HIGH. \overline{BRDYOE} , \overline{BRDYH} , \overline{BRDYIN} and SFUNC are "X" for this table.
- Dout in this case is the same as Din; that is, the input data is written through to the outputs during the write operation.

Truth Table — Match Function(1,2,3)

$\overline{CS1}$	CS2	SFUNC	\overline{OET}	\overline{WET}	\overline{WES}	TAG	VLD ⁽⁴⁾	DTY ⁽⁴⁾	WT ⁽⁴⁾	MATCH	OPERATION
H	X	X	X	X	X	Hi-Z	—	—	—	Hi-Z	Deselected
X	L	X	X	X	X	Hi-Z	—	—	—	Hi-Z	Deselected
L	H	X	X	X	X	—	—	—	—	DOUT	Selected
L	H	X	L	H	X	DOUT	—	—	—	L	Read Tag I/O
L	H	X	H	L	X	DIN	—	—	—	L	Write Tag I/O
L	H	X	X	X	L	—	DIN	DIN	DIN	L	Write Status Bits
L	H	L	H	H	H	TAGIN	L	—	—	L	Invalid Data — Dedicated Status Bits
L	H	L	H	H	H	TAGIN	H	—	—	M	Match — Dedicated Status Bits
L	H	H	H	H	H	TAGIN	X	—	—	M	Match — Generic Status Bits

3075 tbl 04

NOTES:

- "H" = V_{IH}, "L" = V_{IL}, "X" = don't care, "-" = unrelated.
- M = HIGH if TAGIN equals the memory contents at that address; M = LOW if TAGIN does not equal the memory contents at that address.
- \overline{PWRDN} and \overline{RESET} are HIGH for this table. $\overline{W/R}$, BRDYH, \overline{BRDYOE} , \overline{BRDYIN} , \overline{OES} , and CLK are "X".
- This column represents the stored memory cell data for the given Status bit at the selected address.

Truth Table — \overline{BRDY} Function(1,2,3,5)

\overline{BRDYOE}	$\overline{BRDYIN}^{(6)}$	\overline{OET}	\overline{WET}	\overline{WES}	BRDYH	$\overline{W/R}$	SFUNC	VLD ⁽⁴⁾	DTY ⁽⁴⁾	WT ⁽⁴⁾	TAG	MATCH	\overline{BRDY}	OPERATION
H	X	X	X	X	X	X	X	X	—	X	—	—	Hi-Z	\overline{BRDY} Disabled
L	L	X	X	X	X	X	X	X	—	X	—	X	L	Ext \overline{BRDY} Input ⁽⁷⁾
L	H	L	X	X	X	X	X	X	—	X	DOUT	L	H	Read TAG
L	H	X	L	X	X	X	X	X	—	X	DIN	L	H	Write TAG
L	H	X	X	L	X	X	X	DIN	DIN	DIN	—	L	H	Write Status
L	H	X	X	X	H	X	X	X	—	X	—	X	H	Force \overline{BRDY} HIGH
L	H	X	X	X	X	X	L	L	—	X	—	L	H	Invalid TAG
L	H	X	X	X	X	H	L	X	—	H	—	X	H	Write Through
L	H	H	H	H	L	X	L	H	—	L	TAGIN	M	\overline{M}	Compare
L	H	H	H	H	L	L	L	H	—	X	TAGIN	M	\overline{M}	Compare
L	H	H	H	H	L	X	L	H	—	X	TAGIN	M	\overline{M}	Compare
L	H	H	H	H	L	X	H	X	—	X	TAGIN	M	\overline{M}	Compare

3075 tbl 05

NOTES:

- "H" = V_{IH}, "L" = V_{IL}, "X" = don't care, "-" = unrelated.
- M = HIGH if TAGIN equals the memory contents at that address; M = LOW if TAGIN does not equal the memory contents at that address.
- \overline{PWRDN} and \overline{RESET} are HIGH for this table. CLK and \overline{OES} are "X".
- This column represents the stored memory cell data for the given Status bit at the selected address.
- $\overline{CS1}$ is LOW, CS2 is HIGH for this table.
- \overline{BRDYIN} is a synchronous input; thus the inputs noted in the table must be applied during a rising CLK edge.
- \overline{BRDYIN} will be a factor in determining the \overline{BRDY} output in all cases except when BRDYH is HIGH and there is a valid MATCH. In that case, \overline{BRDY} will be LOW(Valid).

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Supply Voltage	4.75	5.0	5.25	V
V _{CCQ}	5V Output Buffers	4.75	5.0	5.25	V
V _{CCQ}	3.3V Output Buffers	3.0	3.3	3.6	V
V _{SS}	Supply Ground	0	0	0	V
V _{IH}	Input High Voltage	2.2	3.0	V _{CC} +0.3	V
V _{IHQ}	I/O High Voltage	2.2	3.0	V _{CCQ} +0.3	V
V _{IL}	Input Low Voltage	-0.5 ⁽¹⁾	—	0.8	V

NOTE: 3075 tbl 06
1. V_{IL} (min.) = -1.5V for pulse width of less than 10ns, once per cycle.

Capacitance (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Condition	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	5	pF
C _{TAG}	TAG Input/Output Capacitance	V _{I/O} = 0V	7	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	7	pF

NOTE: 3075 tbl 07
1. This parameter is determined by device characterization but is not production tested.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Value	Unit
V _{TERM}	Terminal Voltage with Respect to GND	-0.5 to + 7.0 ⁽²⁾	V
T _A	Operating Temperature	0 to +70	°C
T _{BIAS}	Temperature Under Bias	-65 to +135	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _T	Power Dissipation	1.7	W
I _{OUT}	DC Output Current	20	mA

NOTES: 3075 tbl 08
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. V_{IN} should not exceed V_{CC}+0.5V. All pins should not exceed 7.0V. V_{CCQ} should never exceed V_{CC}, and V_{CC} should never exceed V_{CCQ} + 4.0V.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (V_{CC} = 5.0V ± 5%, V_{CCQ} = 5.0V ± 5% or 3.3V ± 0.3V)

Symbol	Parameter	Test Condition	Min.	Max.	Unit
I _L	Input Leakage Current	V _{CC} = Max., V _{IN} = 0V to V _{CC}	—	5	μA
I _{LO}	Output Leakage Current	$\overline{CS1} \geq V_{IH}$, CS2 ≤ V _{IL} , $\overline{OE} \geq V_{IH}$, V _{CC} = Max. V _{OUT} = 0V to V _{CCQ} , V _{CCQ} = Max.	—	5	μA
V _{OL}	Output Low Voltage	I _{OL} = 4mA, V _{CC} = Min.	—	0.4	V
V _{OH}	Output High Voltage	I _{OH} = -4mA, V _{CC} = Min.	2.4	—	V

3075 tbl 09

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,2) (V_{CC} = 5.0V ± 5%)

Symbol	Parameter	Test Condition	71215S8		71215S9		71215S10		71215S12		Unit
			Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
I _{CC}	Operating Power Supply Current	$\overline{PWRDN} \geq V_{IH}$ Outputs Open, V _{CC} = Max., f = f _{MAX} ⁽³⁾	330	—	300	—	290	—	280	—	mA
I _{SB}	Standby Power Supply Current	$\overline{PWRDN} \leq V_{IL}$, V _{IN} ≥ V _{IH} or ≤ V _{IL} V _{CC} = Max., f = f _{MAX} ⁽³⁾	30	—	30	—	30	—	30	—	mA
I _{SB1}	Full Standby Power Supply Current	$\overline{PWRDN} \leq V_{IL}$, V _{IN} ≥ V _{Hc} or ≤ V _{Lc} ⁽⁴⁾ V _{CC} = Max., f = 0 ⁽³⁾	25	—	25	—	25	—	25	—	mA

3075 tbl 10

NOTES:
1. All values are maximum guaranteed values.
2. CS1 ≤ V_{IL}, CS2 ≥ V_{IH}.
3. f_{MAX} = 1/t_{CV} (all address inputs are cycling at f_{MAX}). f = 0 means no address input lines are changing.
4. V_{Hc} = V_{CC} - 0.2V, V_{Lc} = 0.2V

AC Electrical Characteristics

(V_{CC} = 5.0V ± 5%, V_{CCQ} = 5.0V ± 5% or 3.3V ± 0.3V, T_A = 0 to 70°C)

Symbol	Parameter	IDT71215S8		IDT71215S9		IDT71215S10		IDT71215S12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE										
t _{AAT}	Address Access Time Tag Bits	—	10	—	11	—	12	—	14	ns
t _{ACST}	Chip Select Access Time Tag Bits	—	8	—	9	—	10	—	12	ns
t _{CLZ} ⁽¹⁾	Chip Select to Tag and Status Bits in Low-Z	1	—	1	—	1	—	1	—	ns
t _{CHZ} ⁽¹⁾	Chip Select to Tag and Status Bits in High-Z	1	5	1	6	1	6	1	7	ns
t _{OET}	Output Enable to Tag Bits Valid	—	5	—	6	—	6	—	7	ns
t _{OTLZ} ⁽¹⁾	Output Enable to Tag Bits in Low-Z	0	—	0	—	0	—	0	—	ns
t _{OTHZ} ⁽¹⁾	Output Enable to Tag Bits in High-Z	1	5	1	6	1	6	1	7	ns
t _{TOH}	Tag Bit Hold from Address Change	2	—	2	—	2	—	2	—	ns
t _{OES}	Output Enable to Status Bits Valid	—	5	—	6	—	6	—	7	ns
t _{OSLZ} ⁽¹⁾	Output Enable to Status Bits in Low-Z	0	—	0	—	0	—	0	—	ns
t _{OSHZ} ⁽¹⁾	Output Enable to Status Bits in High-Z	1	5	1	6	1	6	1	7	ns
t _{AAS}	Address Access Time Status Bits	—	8	—	9	—	10	—	12	ns
t _{ACSS}	Chip Select Access Time Status Bits	—	6	—	7	—	8	—	10	ns
t _{SOH}	Status Bit Hold from Address Change	2	—	2	—	2	—	2	—	ns

3075 tbl 11

NOTE:

1. This parameter is guaranteed with the AC Load (Figure 3) by device characterization, but is not production tested.

AC Electrical Characteristics⁽¹⁾

(V_{CC} = 5.0V ± 5%, V_{CCQ} = 5.0V ± 5% or 3.3V ± 0.3V, T_A = 0 to 70°C)

Symbol	Parameter	IDT71215S8		IDT71215S9		IDT71215S10		IDT71215S12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
RESET AND POWER DOWN CYCLES										
t _{SR}	$\overline{\text{RESET}}$ Set-up Time	4	—	4	—	4	—	4	—	ns
t _{HR}	$\overline{\text{RESET}}$ Hold Time	1	—	1	—	1	—	1	—	ns
t _{SRST}	Status Bit Reset Time	—	50	—	60	—	60	—	70	ns
t _{SHRS}	Status Bit Hold from $\overline{\text{RESET}}$ LOW	2	—	2	—	2	—	2	—	ns
t _{SMI}	$\overline{\text{RESET}}$ LOW to MATCH and $\overline{\text{BRDY}}$ Invalid	—	9	—	10	—	10	—	12	ns
t _{SMV}	$\overline{\text{RESET}}$ HIGH to MATCH and $\overline{\text{BRDY}}$ Valid	—	110	—	120	—	120	—	130	ns
t _{SHZ} ⁽²⁾	$\overline{\text{RESET}}$ LOW to TAG High-Z	—	9	—	10	—	10	—	12	ns
t _{SLZ} ⁽²⁾	$\overline{\text{RESET}}$ HIGH to TAG Low-Z	—	90	—	100	—	100	—	110	ns
t _{PDSR}	$\overline{\text{PWRDN}}$ Set-up to $\overline{\text{RESET}}$ LOW	30	—	30	—	30	—	30	—	ns
t _{RHPL}	$\overline{\text{RESET}}$ HIGH to $\overline{\text{PWRDN}}$ LOW	1	—	1	—	1	—	1	—	CLK
t _{RHWL}	$\overline{\text{RESET}}$ HIGH to $\overline{\text{WET}}$ and $\overline{\text{WES}}$ LOW	90	—	95	—	95	—	105	—	ns
t _{PD} ⁽²⁾	$\overline{\text{PWRDN}}$ LOW to Low Power Mode	—	50	—	50	—	50	—	50	ns
t _{PU} ⁽²⁾	$\overline{\text{PWRDN}}$ HIGH to Active Power Mode	0	—	0	—	0	—	0	—	ns
t _{PDHZ} ⁽²⁾	$\overline{\text{PWRDN}}$ LOW to Outputs in High-Z	—	9	—	10	—	10	—	12	ns
t _{PDLZ} ⁽²⁾	$\overline{\text{PWRDN}}$ HIGH to Outputs in Low-Z	0	—	0	—	0	—	0	—	ns
t _{PUV}	$\overline{\text{PWRDN}}$ HIGH to Outputs Valid	—	50	—	50	—	50	—	50	ns
t _{WHPL} ⁽²⁾	$\overline{\text{WET}}$ and $\overline{\text{WES}}$ HIGH to $\overline{\text{PWRDN}}$ LOW	5	—	5	—	5	—	5	—	ns
t _{PUWL}	$\overline{\text{PWRDN}}$ HIGH to $\overline{\text{WET}}$ and $\overline{\text{WES}}$ Active	50	—	50	—	50	—	50	—	ns

3075 tbl 12

NOTES:

1. Power-down mode is intended to be used during extended time periods of device inactivity.
2. This parameter is guaranteed with the AC Load (Figure 3) by device characterization, but is not production tested.

AC Electrical Characteristics⁽¹⁾

(V_{CC} = 5.0V ± 5%, V_{CCQ} = 5.0V ± 5% or 3.3V ± 0.3V, T_A = 0 to 70°C)

Symbol	Parameter	IDT71215S8		IDT71215S9		IDT71215S10		IDT71215S12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
WRITE CYCLE AND CLOCK PARAMETERS										
t _{CYC}	Clock Cycle Time	15	—	15	—	15	—	16.6	—	ns
t _{CH} ^(2, 3)	Clock Pulse HIGH	4.5	—	4.5	—	4.5	—	5	—	ns
t _{CL} ^(2, 3)	Clock Pulse LOW	4.5	—	4.5	—	4.5	—	5	—	ns
t _S	\overline{WET} , \overline{WES} , Chip Select, and Input Data Set-up Time	3	—	3	—	3	—	3	—	ns
t _H	\overline{WET} , \overline{WES} , Chip Select, and Input Data Hold Time	1	—	1	—	1	—	1	—	ns
t _{SA}	Address Set-up Time	3	—	3	—	3	—	3	—	ns
t _{HA}	Address Hold Time	1	—	1	—	1	—	1	—	ns
t _{WMI}	CLK HIGH Write to MATCH and \overline{BRDY} Invalid	—	6	—	7	—	7	—	8	ns
t _{CKLZ} ⁽³⁾	CLK HIGH Read to Outputs in Low-Z	1.5	—	1.5	—	1.5	—	1.5	—	ns
t _{CTV} ⁽⁴⁾	CLK HIGH Read to Tag Bits Valid	—	9	—	10	—	10	—	12	ns
t _{CSV} ⁽⁴⁾	CLK HIGH Write to Status Outputs Valid	—	8	—	9	—	9	—	10	ns
t _{CSH} ⁽³⁾	Status Output Hold from CLK HIGH Write	0	—	0	—	0	—	0	—	ns
t _{WHPL}	\overline{WET} and \overline{WES} HIGH to \overline{PWRDN} LOW	5	—	5	—	5	—	5	—	ns
t _{PUWL}	\overline{PWRDN} HIGH to \overline{WET} and \overline{WES} Active	50	—	50	—	50	—	50	—	ns

3075 tbl 14

NOTES:

1. All Write cycles are synchronous and referenced from rising CLK.
2. This parameter is measured as a HIGH time above 2.0V and a LOW time below 0.8V.
3. This parameter is guaranteed with the AC Load (Figure 3) by device characterization, but is not production tested.
4. Addresses are stable prior to CLK transition HIGH.

AC Electrical Characteristics

(VCC = 5.0V ± 5%, VCCQ = 5.0V ± 5% or 3.3V ± 0.3V, TA = 0 to 70°C)

Symbol	Parameter	IDT71215S8		IDT71215S9		IDT71215S10		IDT71215S12		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
MATCH AND $\overline{\text{BRDY}}$ CYCLES										
tADM	Address to MATCH Valid	—	8	—	9	—	10	—	12	ns
tDAM	Data Input to MATCH Valid	—	8	—	9	—	10	—	12	ns
tCSM	Chip Select to MATCH Valid	—	8	—	9	—	10	—	12	ns
tCMLZ ⁽¹⁾	Chip Select to MATCH in Low-Z	1	—	1	—	1	—	1	—	ns
tCMHZ ⁽¹⁾	Chip Select to MATCH in High-Z	1	5	1	6	1	6	1	7	ns
tMHA	MATCH Valid Hold from Address	2	—	2	—	2	—	2	—	ns
tMHD	MATCH Valid Hold from Data	2	—	2	—	2	—	2	—	ns
tBHA	$\overline{\text{BRDY}}$ Valid Hold from Address	2	—	2	—	2	—	2	—	ns
tBHD	$\overline{\text{BRDY}}$ Valid Hold from Data	2	—	2	—	2	—	2	—	ns
tADB	Address to $\overline{\text{BRDY}}$ Valid	—	9	—	10	—	11	—	13	ns
tDAB	Data Input to $\overline{\text{BRDY}}$ Valid	—	9	—	10	—	11	—	13	ns
tCSB	Chip Select LOW to $\overline{\text{BRDY}}$ Valid	—	9	—	10	—	11	—	13	ns
tOEBV	$\overline{\text{BRDYOE}}$ LOW to $\overline{\text{BRDY}}$ Valid	—	6	—	6	—	7	—	8	ns
tOBLZ ⁽¹⁾	$\overline{\text{BRDYOE}}$ LOW to $\overline{\text{BRDY}}$ in Low-Z	0	—	0	—	0	—	0	—	ns
tOBHZ ⁽¹⁾	$\overline{\text{BRDYOE}}$ HIGH to $\overline{\text{BRDY}}$ in High-Z	1	5	1	6	1	6	1	7	ns
tBYFH	BRDYH HIGH to Force $\overline{\text{BRDY}}$ HIGH	—	5	—	5	—	5	—	6	ns
tBYHV	BRDYH LOW to $\overline{\text{BRDY}}$ Valid	—	5	—	5	—	5	—	6	ns
tSB	$\overline{\text{BRDYIN}}$ Set-up Time	4	—	4	—	4	—	4	—	ns
tHB	$\overline{\text{BRDYIN}}$ Hold Time	1.5	—	1.5	—	1.5	—	1.5	—	ns
tBIBL	CLK HIGH $\overline{\text{BRDYIN}}$ LOW to $\overline{\text{BRDY}}$ LOW	—	6	—	6	—	7	—	8	ns
tBIBV	CLK HIGH $\overline{\text{BRDYIN}}$ HIGH to $\overline{\text{BRDY}}$ Valid	—	6	—	6	—	7	—	8	ns
tOEMI	$\overline{\text{OET}}$ LOW to MATCH and $\overline{\text{BRDY}}$ Invalid	—	6	—	7	—	7	—	8	ns
tOEMV	$\overline{\text{OET}}$ HIGH to MATCH and $\overline{\text{BRDY}}$ Valid	—	7	—	8	—	8	—	10	ns
tWRBH ⁽²⁾	$\overline{\text{WR}}$ HIGH to $\overline{\text{BRDY}}$ HIGH	—	6	—	7	—	7	—	8	ns
tWRBV ⁽²⁾	$\overline{\text{WR}}$ LOW to $\overline{\text{BRDY}}$ Valid	—	6	—	7	—	7	—	8	ns
tWMI	CLK HIGH Write to MATCH and $\overline{\text{BRDY}}$ Invalid	—	7	—	7	—	7	—	8	ns
tWMV ⁽³⁾	CLK HIGH Read to MATCH and $\overline{\text{BRDY}}$ Valid	—	8	—	9	—	10	—	12	ns

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NOTES:

1. This parameter is guaranteed with the AC Load (Figure 3) by device characterization, but is not production tested.
2. These parameters only apply when SFUNC is LOW and the internal WT bit is HIGH.
3. tADM, tDAM, tCSM and tADB, tDAB, tCSB must also be satisfied.

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Timing Reference Levels	1.5V
AC Test Load	See Figures 1, 2, 3, & 4

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AC Test Loads

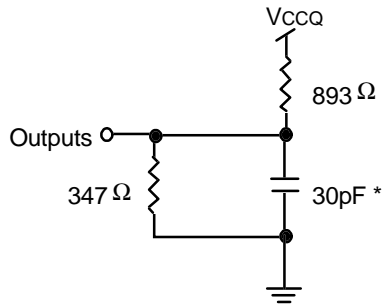


Figure 1. AC Test Load

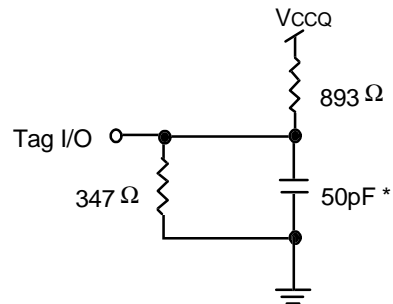


Figure 2. Tag I/O AC Test Load

3075 drw 03

3075 drw 04

* Including scope and jig capacitance

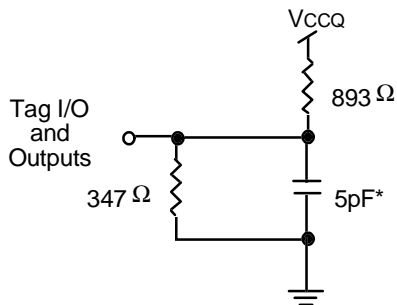
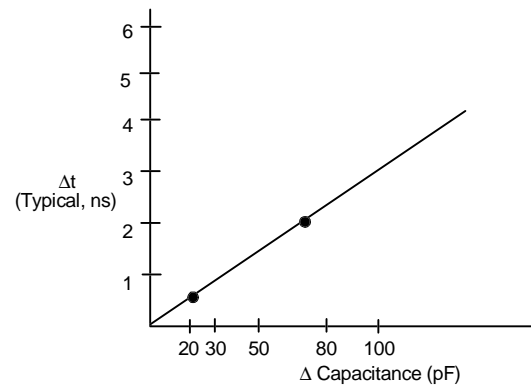


Figure 3. AC Test Load
(for thz and tlz parameters)

3075 drw 05

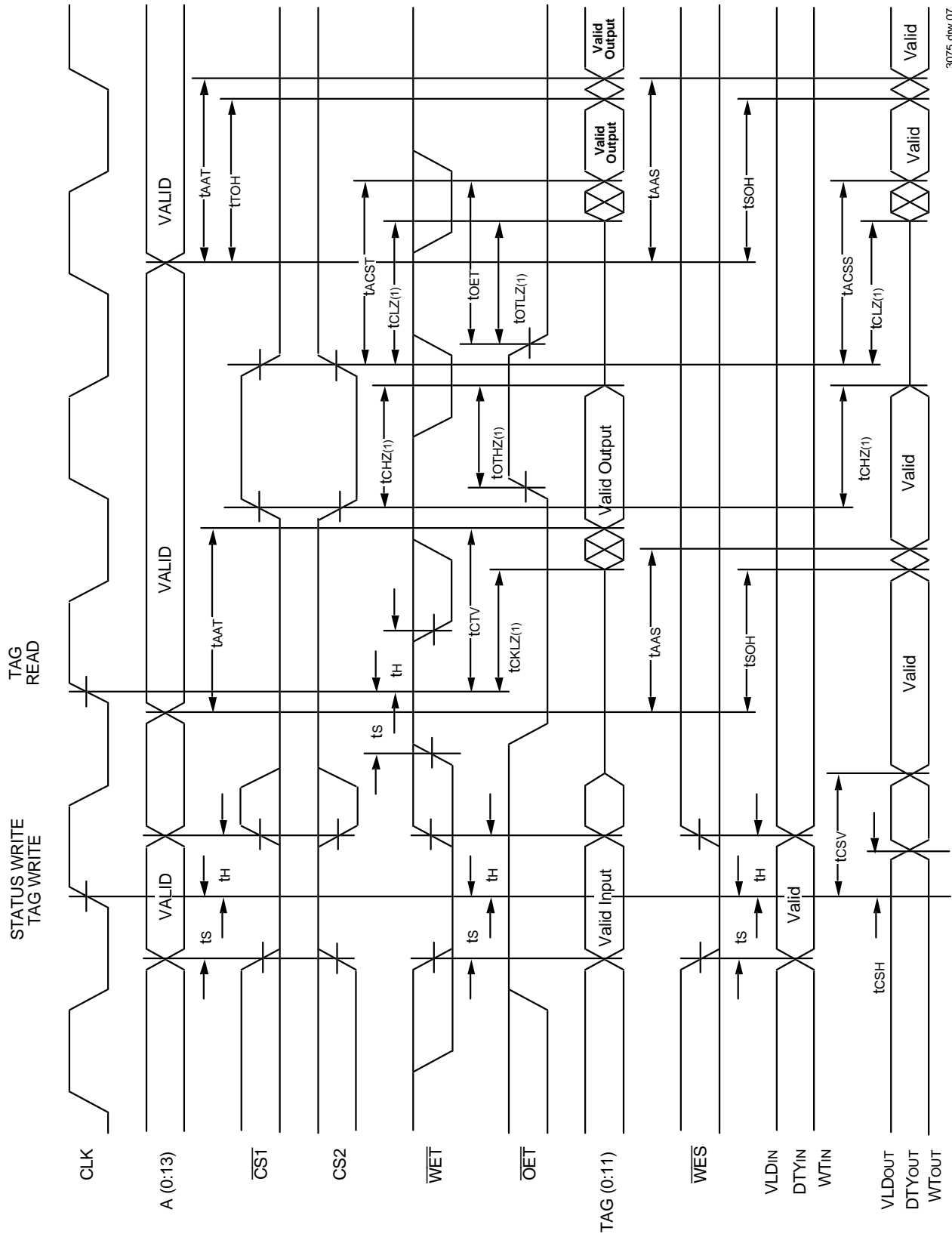


3075 drw 06

* Including scope and jig capacitance

Figure 4. Lumped Capacitance Load, Typical Derating

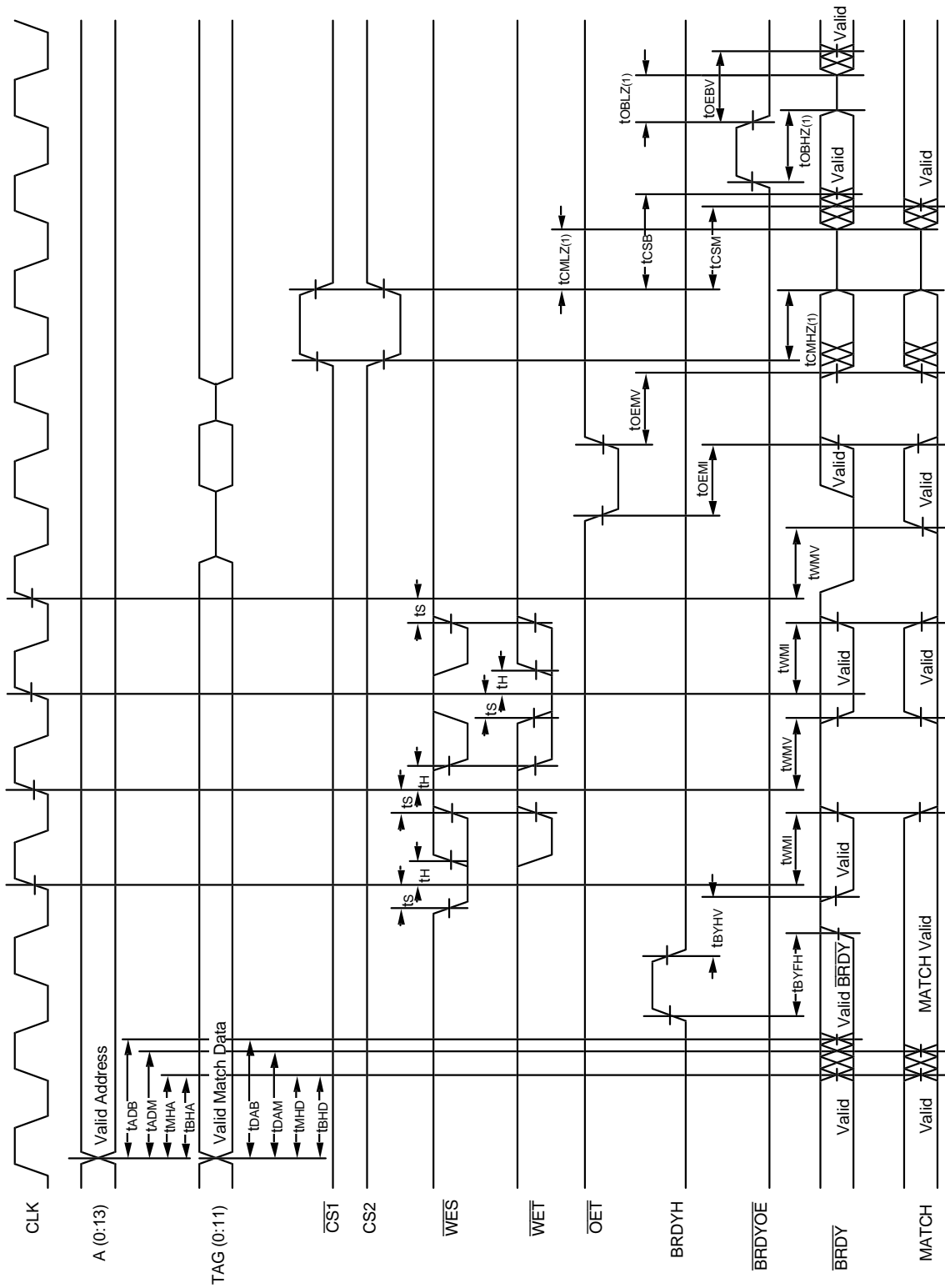
Timing Waveforms of Write and Read Cycles



3075 dhw 07

NOTE:
 1. Transition is measured $\pm 200\text{mV}$ from steady state.

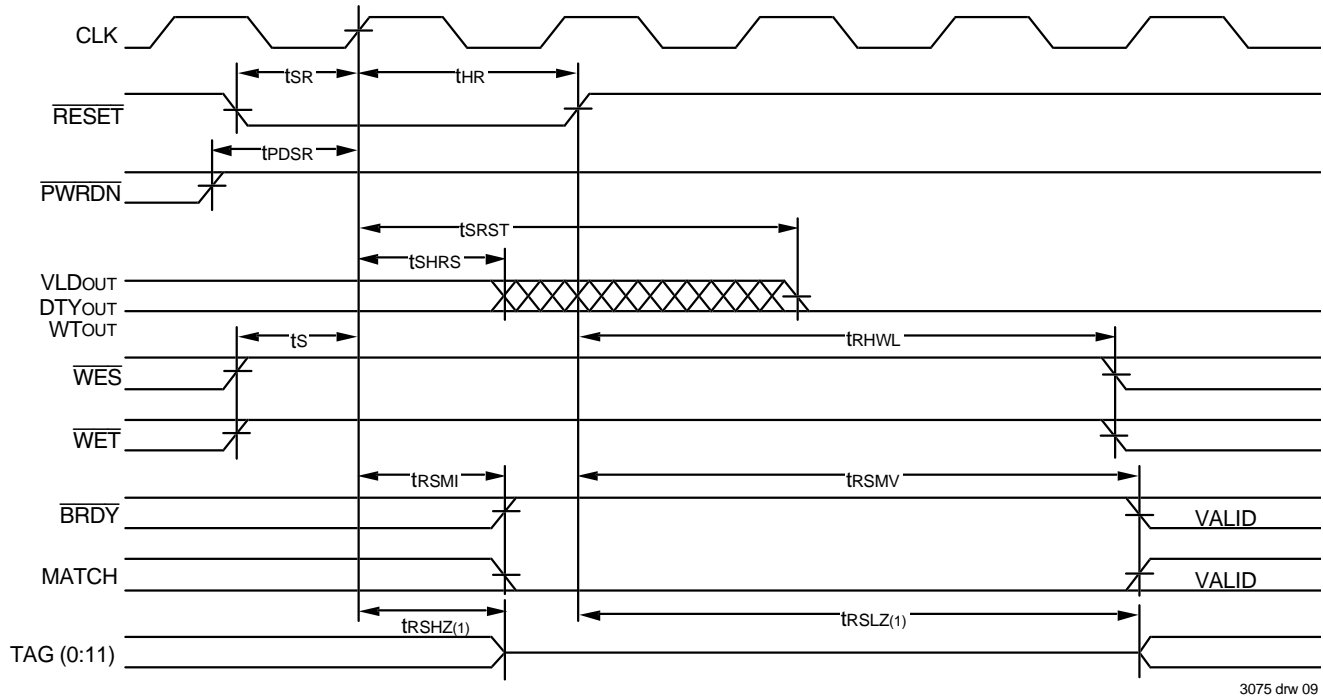
Timing Waveforms of Match and BRDY Functions



3075 dnv 08

NOTE:
 1. Transition is measured ±200mV from steady state.

Timing Waveforms of $\overline{\text{RESET}}$ Function

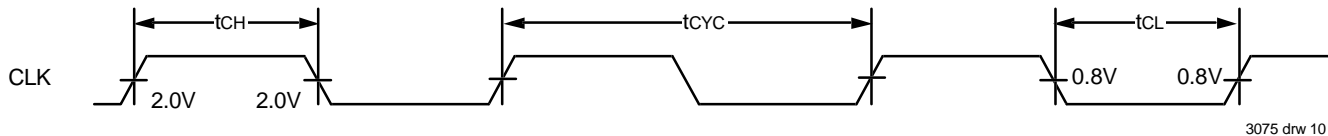


3075 drw 09

NOTE:

1. Transition is measured $\pm 200\text{mV}$ from steady state.

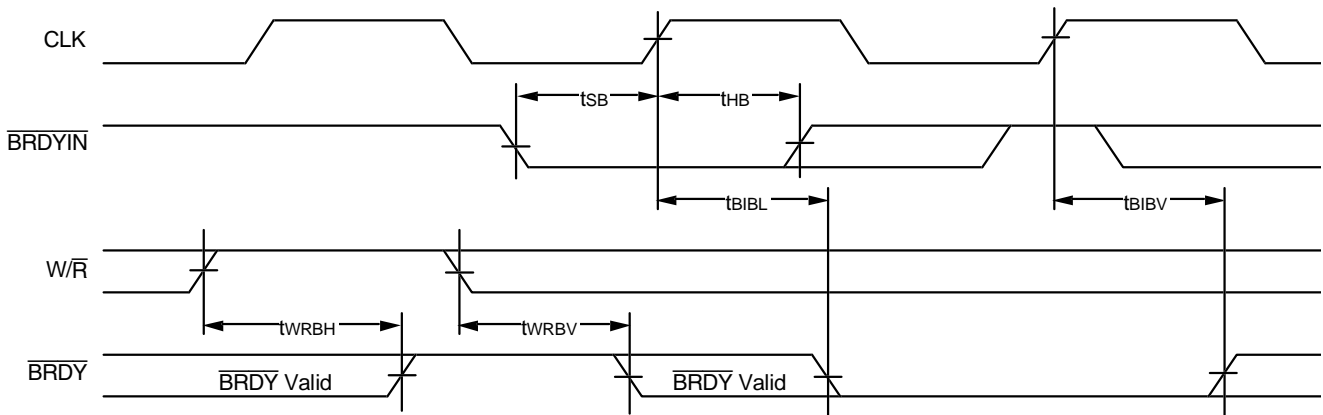
Clock Timing Waveform



3075 drw 10

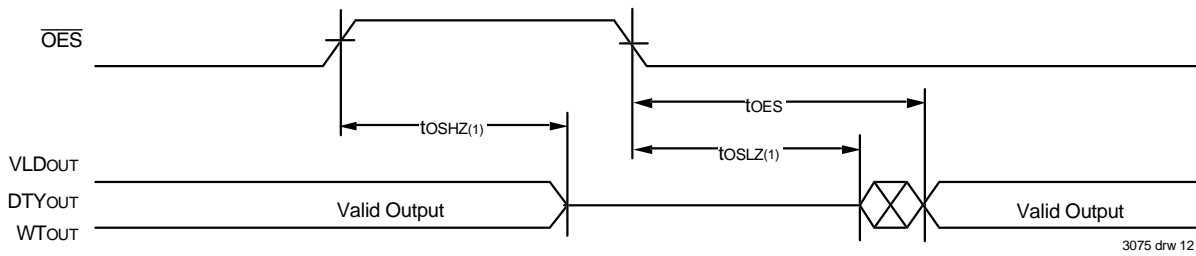
Timing Waveforms of $\overline{\text{BRDY}}$ and $\overline{\text{W/R}}$ Signal

Applies when SFUNC is LOW, and the internal WT bit is HIGH



3075 drw 11

Timing Waveforms of $\overline{\text{OES}}$ Function

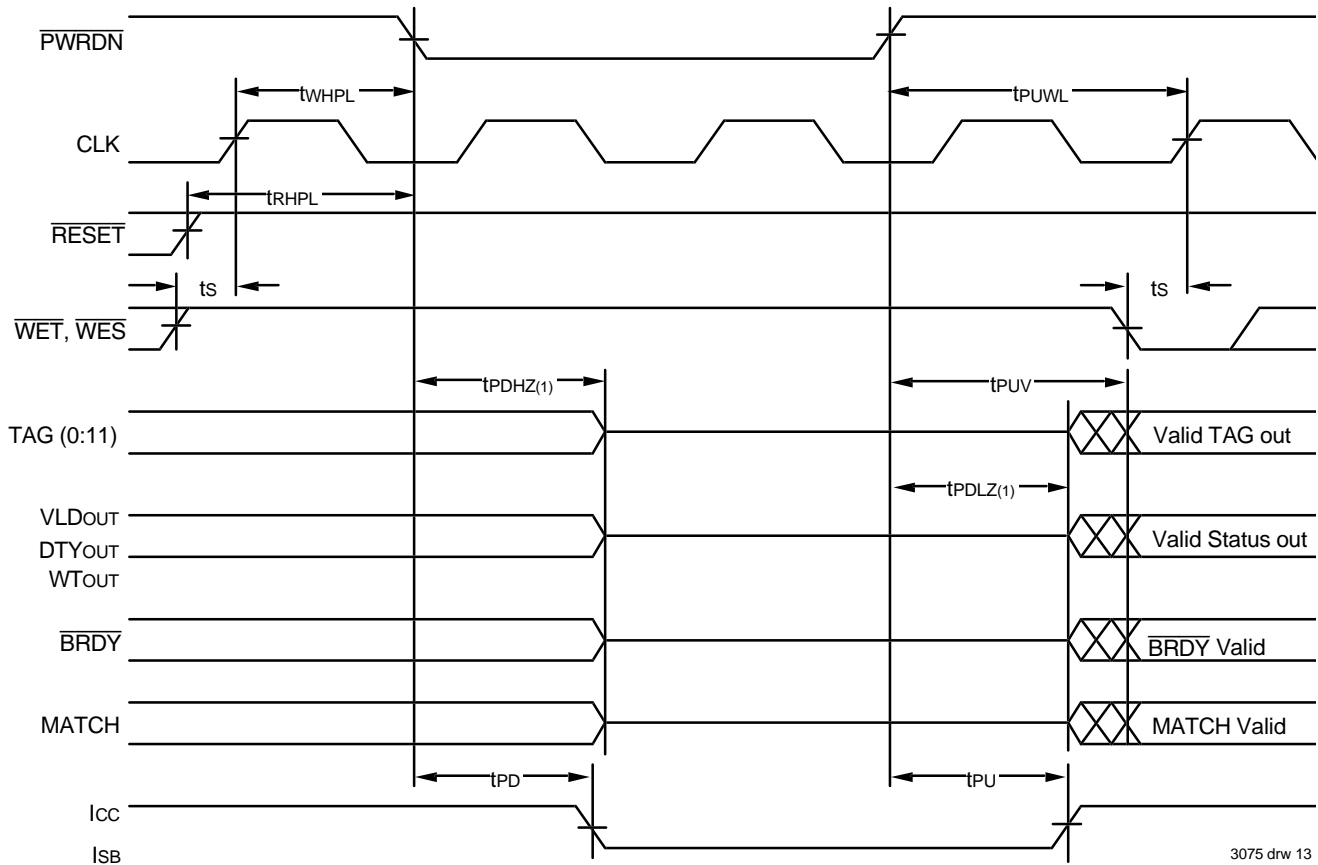


3075 drw 12

NOTE:

1. Transition is measured $\pm 200\text{mV}$ from steady state.

Timing Waveforms of POWER DOWN Function



3075 drw 13

NOTE:

1. Transition is measured $\pm 200\text{mV}$ from steady state.

Ordering Information

IDT	<u>71215</u>	<u>S</u>	<u>XX</u>	<u>PF</u>	
	Device Type	Power	Speed	Package	
				PF	Plastic Thin Quad Flatpack (PN80-1)
				8	} Speed in nanoseconds
				9	
				10	
				12	

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Datasheet Document History

10/19/99		Updated to new format
	Pg. 15	Added datasheet document history

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